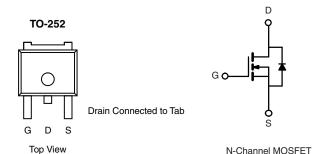


# Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.0032				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.0039				
I <sub>D</sub> (A)	100				
Configuration	Single				



#### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- AEC-Q101 Qualified<sup>d</sup>
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



COMPLIANT HALOGEN

ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD100N03-3m2L-GE3			

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	30	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	v	
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C		100		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	89		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	100	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	150		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	60		
Single Pulse Avalanche Energy		E <sub>AS</sub>	180	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D-	136	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	45	٧V	
Operating Junction and Storage Temperature Rar	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.1	0/10	

#### Notes

a. Package limited.

b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$ 

c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

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# SQD100N03-3m2L



Vishay Siliconix

PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static					•			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$		30	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$		2.0	2.5	v	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 175 °C	-	-	150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.0027	0.0032		
Drain Source On State Desistence?	Р	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0049	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0058		
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 15 A	-	0.0031	0.0039		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		-	122	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		r <sub>GS</sub> = 0 V V <sub>DS</sub> = 15 V, f = 1 MHz	-	5053	6316	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	921	1151		
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	377	471		
Total Gate Charge <sup>c</sup>	Qg			-	77	116		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 V$	$V_{DS} = 15 \text{ V}, I_{D} = 50 \text{ A}$	-	14.3	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	11	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.14	2.28	3.42	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	10	15		
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:V_DD} \begin{array}{l} V_{\text{DD}} = 15 \ \text{V}, \ R_{\text{L}} = 0.3 \ \Omega \\ I_{\text{D}} \cong 50 \ \text{A}, \ V_{\text{GEN}} = 10 \ \text{V}, \ R_{g} = 1 \ \Omega \end{array}$		-	10	15		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	42	63	ns -	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	10	15		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	150	А	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	40 A, V <sub>GS</sub> = 0 V	-	0.85	1.2	V	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

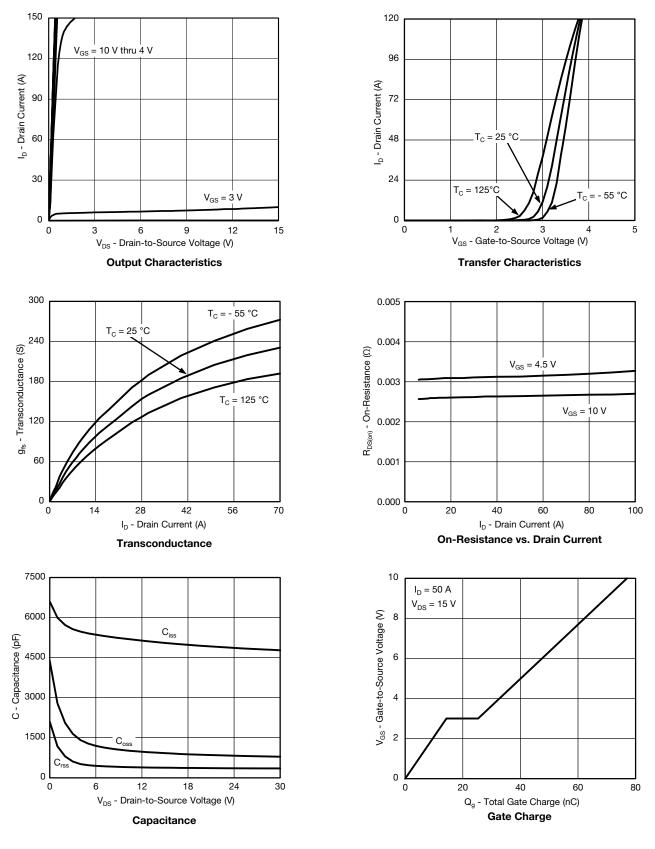
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



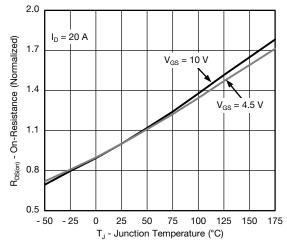
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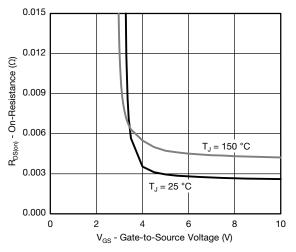
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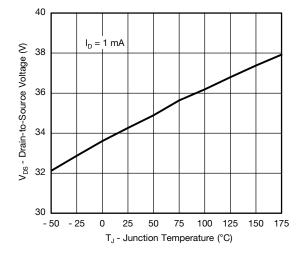
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



**On-Resistance vs. Junction Temperature** 



On-Resistance vs. Gate-to-Source Voltage

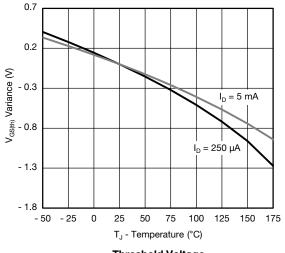


Drain Source Breakdown vs. Junction Temperature

10 T<sub>1</sub> = 150 °C I<sub>s</sub> - Source Current (A) 1 0.1 T<sub>J</sub> = 25 °C 0.01 0.001 0.0 0.2 0.4 0.6 0.8 1.0 1.2 V<sub>SD</sub> - Source-to-Drain Voltage (V)

100

Source Drain Diode Forward Voltage





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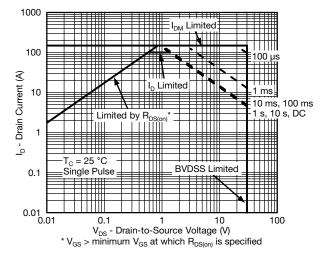
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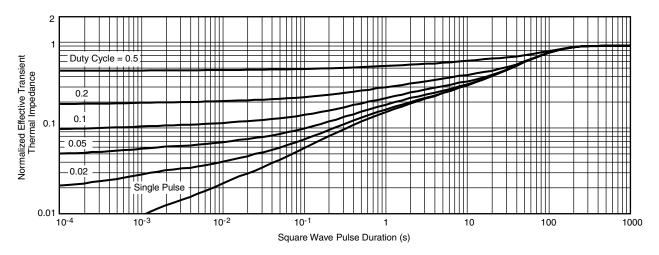




### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Safe Operating Area

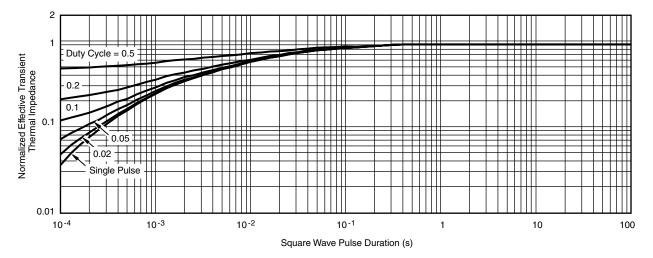


Normalized Thermal Transient Impedance, Junction-to-Ambient





## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

The characteristics shown in the two graphs

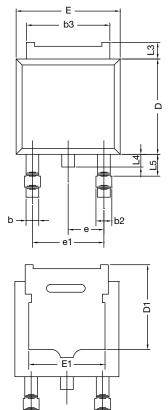
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

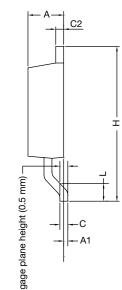
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?62573</u>.





# **TO-252AA Case Outline**



	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

Note

• Dimension L3 is for reference only.

Ф **Т** 



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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